

AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph on page 4, line 10 as follows:

(iii) the flow amount ratio of the reactive gas to the inert gas is $50\% \leq \frac{\text{reactive gas}}{\text{reactive gas} + \text{inert gas}} \leq 80\%$ and, preferably, N₂O is used as the reactive gas and Ar is used as the inert gas.

Please replace paragraph on page 7, line 32 through page 8, line 3 as follows:

This sputtering unit 1000 [[500]] includes a low pressure vacuum tank 3. The vacuum tank 3 has a reactive gas inlet 14a, an inert gas inlet 14b and a mixture gas inlet 14c. In addition, it has two vacuum exhaust outlets 14d and a vacuum exhaust outlet 14e. It also has a target electrode 5 and a substrate holder 7.

Please replace paragraph on page 21, line 2 as follows:

In addition, a phase shift film, which has a high quality of 8% or more of transmittance, can be gained in the samples TO6 to TO9 and in TA1 and TA2 ~~to TA3~~ with respect to a KrF laser (248nm).

Please replace paragraph on page 21, line 16 as follows:

As shown in Tables 6 and 7 as well as in Figs. 2 and 3, in the case that the reactive gas is introduced in the mixed condition, though a phase shift film which has such a high quality as in Evaluation 1 cannot be gained, it is possible to form a phase shift film of which the transmittance is relatively high such that the transmittance of the sample TMX3 is 4.471% [[4.741%]] with respect to an ArF laser (193nm) and the transmittance of the sample TMX3 is 5.327% with respect to a KrF laser (248nm).